What is Claimed:

1		1.	A process for manufacturing an integrated circuit package			
2	comprising:					
3		(a)	providing a substrate having a first dielectric layer, a conductive			
4	layer above th	e first	dielectric Jayer, and a second dielectric layer above the conductive			
5	layer, the second dielectric layer having a cavity exposing a portion of the conductive					
6	layer; and					
7		(b)	interconnecting an integrated circuit directly to the exposed portion			
8	of the conductive layer in the cavity.					
1		2.	The method of claim 1 wherein step (b) comprises:			
2		coupl	ing a conductor to a bond pad formed on the integrated circuit; and			
3	connecting the conductor directly to the conductive layer.					
1		3.	The method of claim 1 further comprising providing one of a			
2	ground plane and a power plane in the exposed portion of the conductive layer.					
1		4.	The method of claim 3 further comprising providing at least one			
2	connection for a signal line in the exposed portion of the conductive layer.					
1		5.	The method of claim 1 further comprising providing at least one			
2	connection for a signal line in the exposed portion of the conductive layer.					
1		6.	The method of claim 1 further comprising forming multiple			
2	interconnections between the integrated circuit chip and the conductive layer.					
1		7.	A method of manufacturing a substrate adapted to receive an			
2	integrated circuit chip comprising:					
3		(a)	providing a first dielectric layer;			
4		(b)	providing a conductive layer above the first dielectric layer;			
5		(c)	providing a second dielectric layer above the conductive layer; and			
6		(d) fo	rming a cavity in the second dielectric layer to expose a portion of			



7

the conductive layer.





1		8.	The method of claim 7 wherein steps (a), (b), and (c) occur prior to		
2	step (d).				
1		9.	The method of claim 7 further comprising:		
2		provid	ding a contact area to a ground plane by exposing the portion of the		
3	conductive lay	yer.			
1		10.	The method of claim 7 further comprising:		
2		(e) for	rming plated through holes in the substrate.		
1		11.	The method of claim 10 wherein step (e) is performed prior to step		
2	(d).				
1		12.	A method of manufacturing an integrated circuit package		
2	comprising:				
3		provid	ling the substrate of claim 7; and		
4		coupli	ing the integrated circuit chip to the substrate.		
1		13.	A method of manufacturing a substrate adapted to receive an		
2	integrated circuit chip comprising:				
3		(a)	providing a first dielectric layer;		
4		(b)	providing a first conductive layer above the dielectric layer;		
5		(c)	providing a second dielectric layer above the first conductive layer		
6		(d)	providing a second conductive layer above the second dielectric		
7	layer;				
8			rming a cavity in a first region of the second dielectric layer to		
9	expose a porti	on of tl	he first conductive layer.		
1		14.	The process of claim 13 wherein step (d) further comprises		
2	providing the	second	conductive layer on regions other than the first region.		
1		15.	The process of claim 13 wherein step (d) further comprises		
2	removing a po	ortion o	f the conductive layer formed above the first region.		
1		16.	A method of manufacturing an integrated circuit package		
2	comprising:				

Sul



3	providing the substrate of claim 13; and
4	coupling the integrated circuit chip to the substrate.
5	17. A process for manufacturing an integrated circuit package
6	comprising:
7	(a) receiving a substrate having a first dielectric layer, a conductive
8	layer above the first dielectric layer, and a second dielectric layer above the conductive
9	layer, the second dielectric layer having a cavity exposing a portion of the conductive
0	layer; and
1	(b) interconnecting an integrated circuit directly to the exposed portion
2	of the conductive layer in the cavity.